



PATENT
740756-1881

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Hongyong ZHANG et al.

Application No.: 09/190,618

Filed: November 12, 1998

For: SEMICONDUCTOR DEVICE AND METHOD
FOR FABRICATING THE SAME

Art Unit: 2815

Examiner: E. LEE

CERTIFICATE OF MAILING T. Flowers

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AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

September 24, 2001

Dear Sir:

In response to the Examiner's non-Final Office Action mailed May 23, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE SPECIFICATION:

Please substitute the current specification with another copy of the specification attached herewith.

IN THE CLAIMS:

Please amend claims 17, 18 and 20 as follows:

17. (Amended) A semiconductor device according to claim 16 wherein a width of the pair of second regions between the channel forming region and the pair of first regions in said first thin film transistor is within a range from 0.4 to 2 μm .

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